

Supplementary Information

**Synthesis of nitrogen-doped graphene by pyrolysis of
ionic-liquid-functionnalized graphene**

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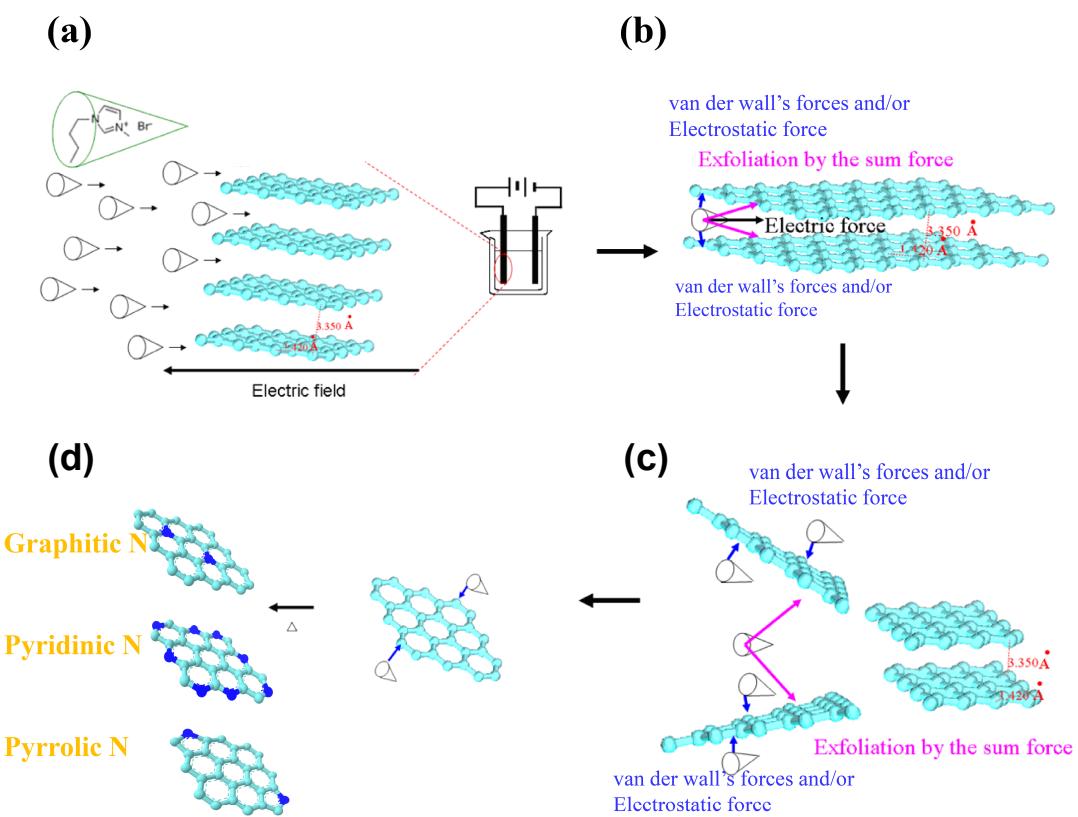
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Experiment

Two high-purity graphite rods were purchased from China National Medicines Shenyang Co. Ltd.. The ILs 1-butyl-3-methylimidazolium bromide ([Bimi][Br]), 1-butyl-3-methylimidazolium hexafluorophosphate ([Bmim][PF₆]) and 1-butyl-3-methylimidazolium acetate ([Bmim][Ac]), dimethyl sulfoxide (DMSO, 99%), ethanol (C₂H₅OH, 99%), hydrogen bromide (HBr, 99%) and ammonium (NH₄OH, 33%) were obtained from Fisher Scientific (USA). All stock solutions were prepared using deionized water without further purification. Two high-purity graphite rods were placed parallel with a separation of 1.0 cm, were inserted as electrodes into the electrolyte (IL: solvent = 1:10). AYJ26K model potentiostat (Yongheng Precision Ammeter Co., China) was used to provide the potential. Static potentials of 15V were applied to the two electrodes. After 3 hours, the anode graphite rod was exfoliated and then a black precipitate gradually appeared at the bottom of the reactor. The precipitate was washed by water and dried at 60 °C and thermal annealing in N₂ atmosphere for 4 h at 400 °C to obtain NG.

Transmission electron microscopy (TEM) images were obtained with a Hitachi model H-800 TEM opened at an accelerating voltage of 100 kV. XPS of the NG was obtained with a Physical Electronics Quantum 2000 scanning ESCA microprobe. AFM images were obtained with an atomic force microscope (Nanoscope III, Digital Instrument). The Raman spectra of the products were recorded at ambient temperature on a Raman spectroscopy (Horiba HR800, with laser excitation at 514.5 nm, 2 mW power). X-ray powder diffraction (XRD) measurements of the as-prepared sample were performed on a Rigaku D/max-II B X-ray diffractometer with Cu K α radiation (λ = 0.15418 nm), and the electrochemical measurements were carried out at room temperature (25 ± 2 °C).



Scheme S1. Schematic of the synthesis of N-doped graphene from graphite: (a) Anions in ILs were pulled by anode; whereas cations in ILs were pulled to anode, (b) The cations were inserted into each layer of graphite and exfoliated by the summed force of electric force, Van der Wall's forces, and electrostatic force, (c) ionic-liquid-functionalized graphene was obtained, (d) Thermal annealing to yield NG with different N-doping configuration.

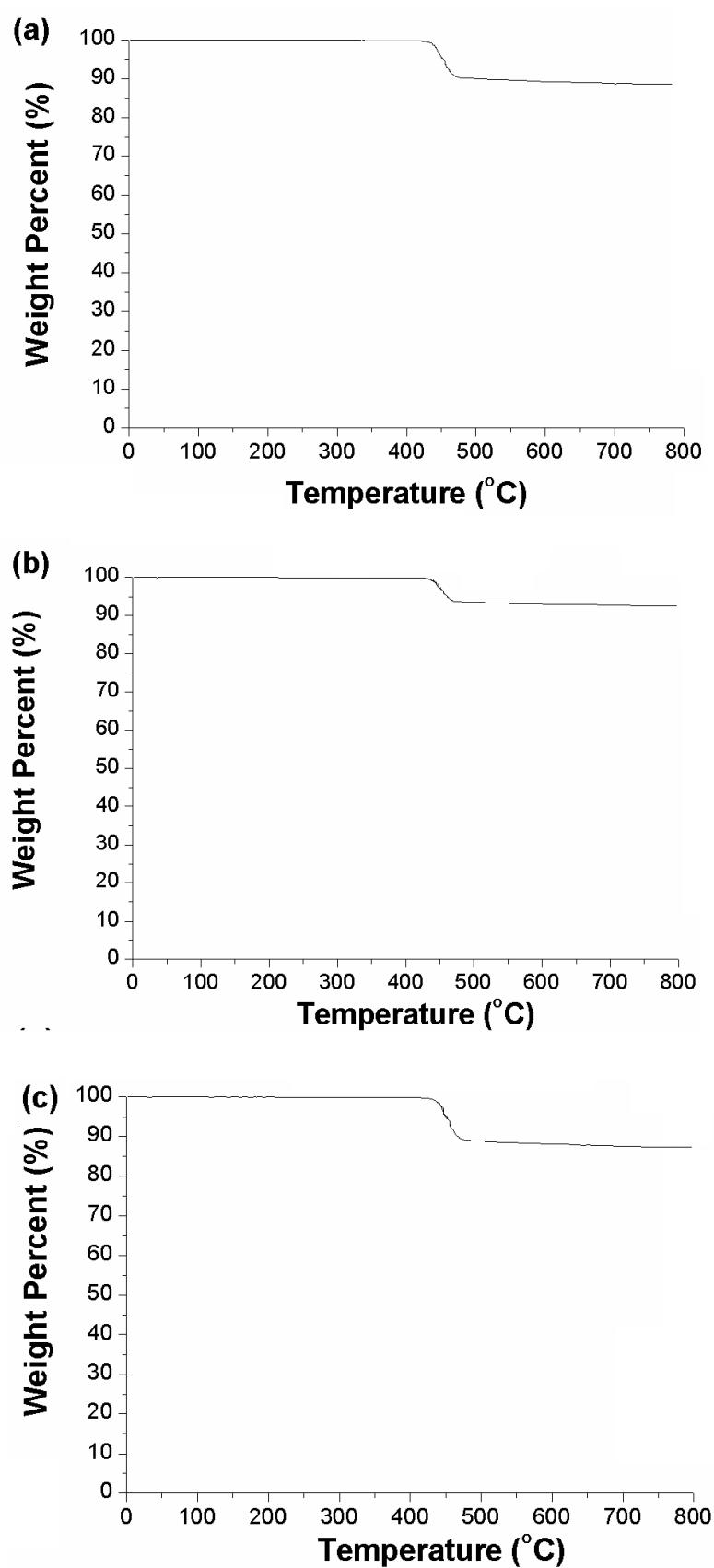


Fig. S1. TGA curve of N-doped graphene synthesized using (a) [Bmim]Br; (b) [Bmim][PF₆] and (c) [Bmim]Ac.

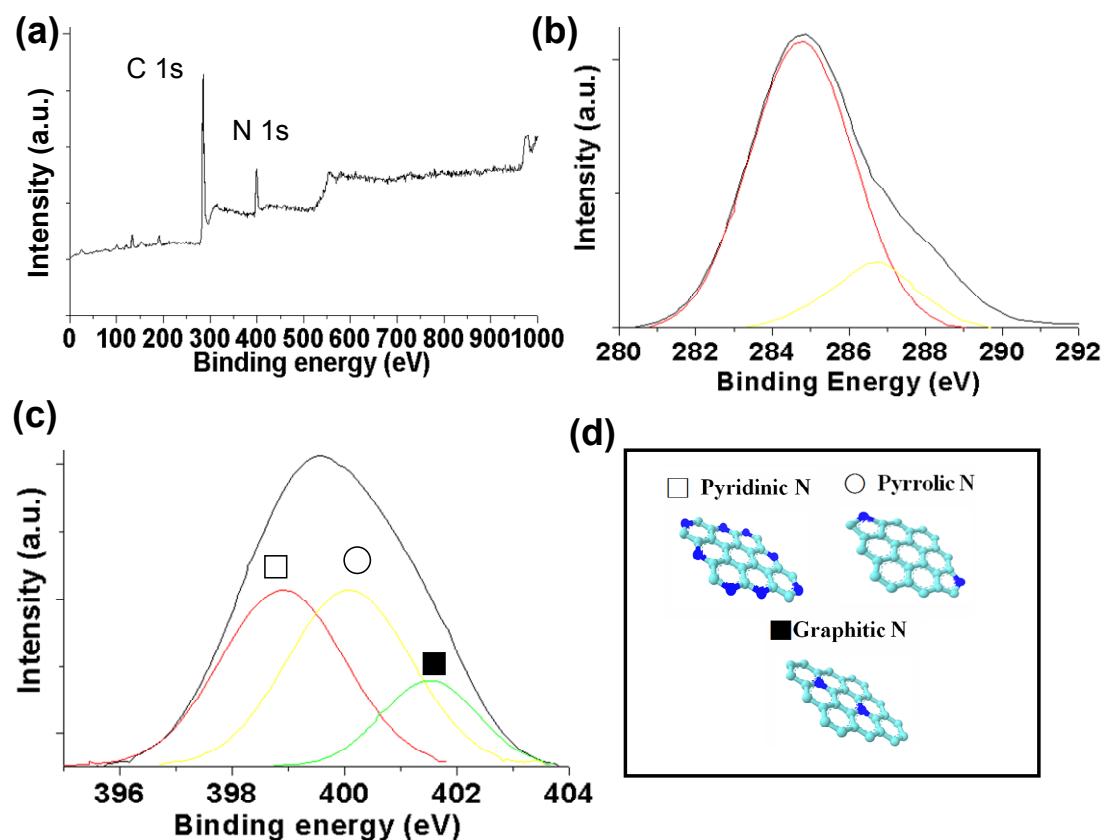


Fig. S2 The XPS spectra of NG synthesized using [Bmim][PF₆] (a) Survey, (b) High resolution C 1s, (c) High resolution N1s, and (d) Schematic illustration of N-doping configurations.

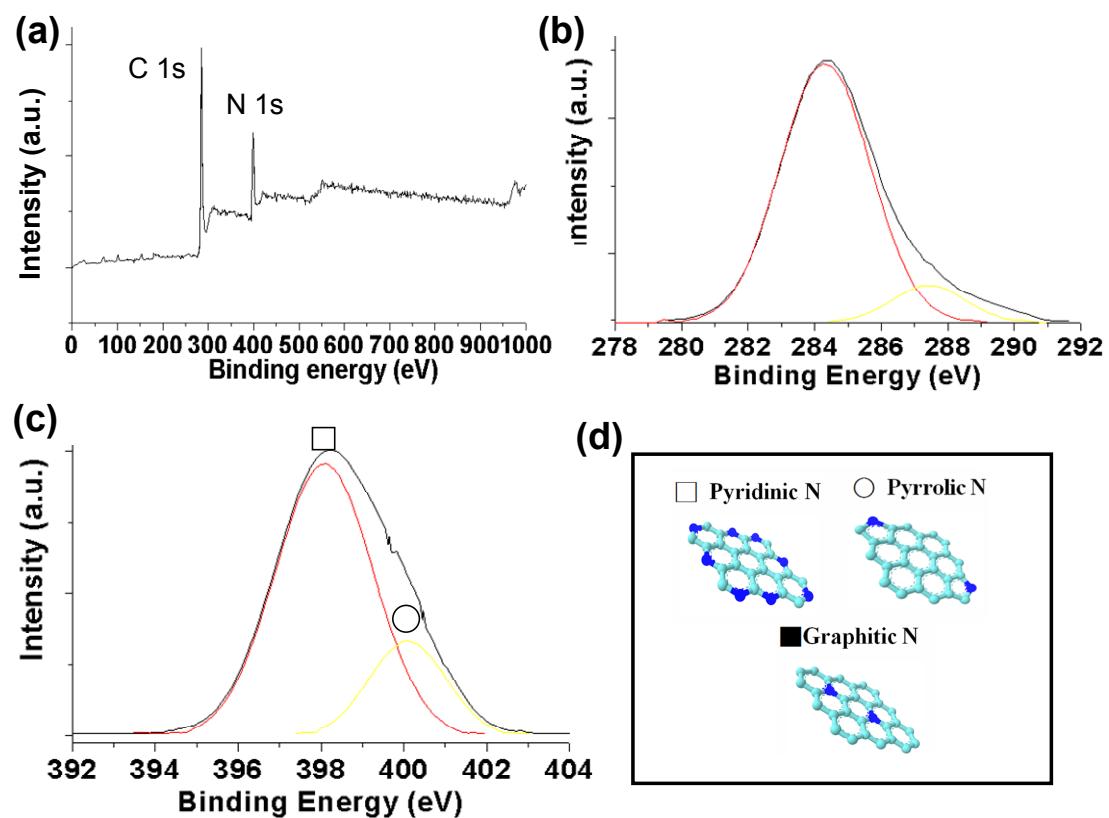


Fig. S3 The XPS spectra of NG synthesized using [Bmim]Ac (a) Survey, (b) High resolution C1s, (c) High resolution N1s, and (d) Schematic illustration of N-doping configurations.

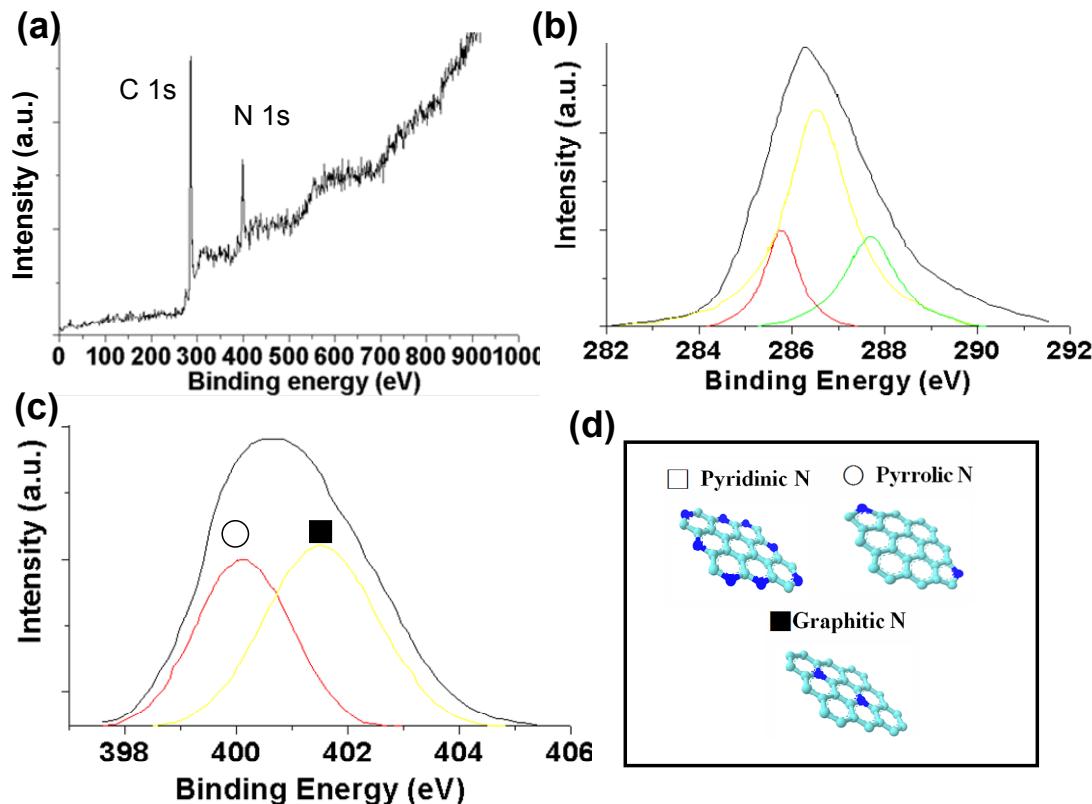


Fig. S4 The XPS spectra of NG synthesized using [Bmim]Br in HBr at pH 2.0 (a) Survey, (b) High resolution C1s spectra, (c) High resolution N1s spectra, and (d) schematic illustration of N-doping configurations.

Table S1: The percentage of nitrogen/carbon in NG synthesized using (a) [Bmim][Br], (b) [Bmim][PF₆], and (c) [Bmim][Ac] determined by CHN analysis and XPS equation.

ILs used	N/C (%) by XPS	N/C (%) by elemental analysis
[Bmim][Br]	21.6	21.4
[Bmim][PF ₆]	15.6	15.8
[Bmim][Ac]	22.1	21.9

FTIR and NMR spectra of NG

The FTIR spectra ($500\text{--}4000\text{ cm}^{-1}$) were obtained using a Nicolet IR100 FTIR spectrometer. Generally, the graphite peak at about 3405 cm^{-1} is related to the O-H stretching. The absorption peak at 1737cm^{-1} is related to the C=O stretching of COOH groups at the edges of the GO sheets. The peak at 1627 cm^{-1} is due to the H–O–H bending of absorbed water. The peaks at 1386 and 1057 cm^{-1} are due to tertiary C-OH groups and C-O, respectively. The peaks of the N-doped graphene between 1647 cm^{-1} can be assigned to the sp₂ C=N and/or C=C, and the peak at 1259 , 1393 , and 1527 cm^{-1} are related to the sp₃ N-H.

High-resolution solid-state ^{13}C NMR experiments were carried out on a JEOL ECA400 spectrometer operated at 100.53 MHz using the single-pulse decoupling method. The solid-state ^{13}C NMR spectra with the ^1H decoupling of graphite and N-doped graphene are measured. The graphite contains four peaks at 60 , 70 , 110 , and 130 ppm , which are assigned to C-O-C epoxide groups, C-OH groups, and conjugated double bonds in oxidized aliphatic rings and aromatic entities, respectively. The N-doped graphene only contains one peak centered at 120 ppm , suggesting that aromatic entities have remained greatly.

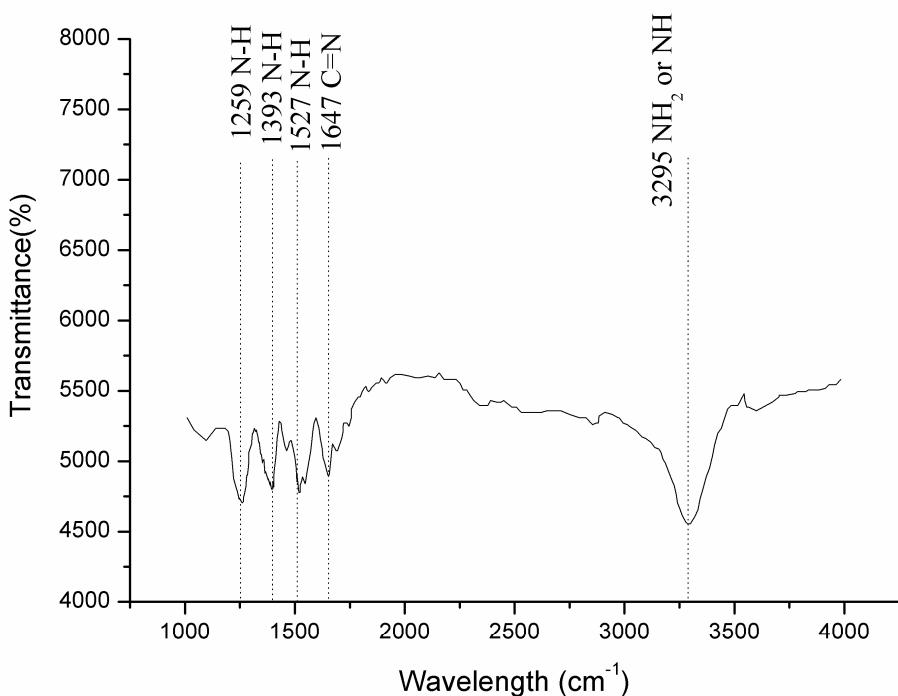


Fig. S5 FTIR spectrum of NG synthesized using [Bmim][Br].

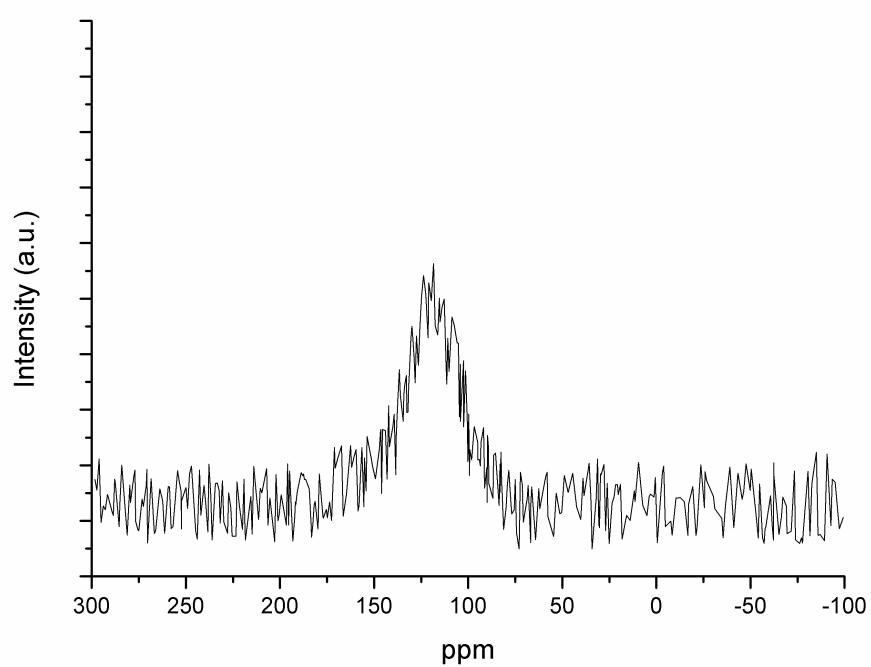


Fig. S6 NMR spectrum of NG synthesized using [Bmim][Br].

Raman

We calculated the Raman spectrum of nanoscale ordered structure to which Raman spectrum is sensitive with the package for first-principles computations ABINIT (URL <http://www.abinit.org>). Depending on the frequency of incident laser light we known the light scattering changed called as Raman effect by normal vibration on target molecular symmetry. The intensity and frequency of Raman spectrum varied with the lattice dynamics, such as phonon frequency, mass, and Raman tensor. We simulate the Raman spectrum with ABINIT, which is a joint project between the Université Catholique de Louvain, Corning Incorporated, and other contributors. The first-principles calculation optimization was performed and finally damping constant ($\Gamma_i = 10 \text{ cm}^{-1}$), 8x8x1 Monkhorst-pack grid, ECUT=45 Ha and tolwfr = 10^{-18} were used. The disorder from O or N atoms insertion in the entire Brillouin zone determined the width of Raman bands with the corresponding phonon band.

Raman shift simulation of D and G band

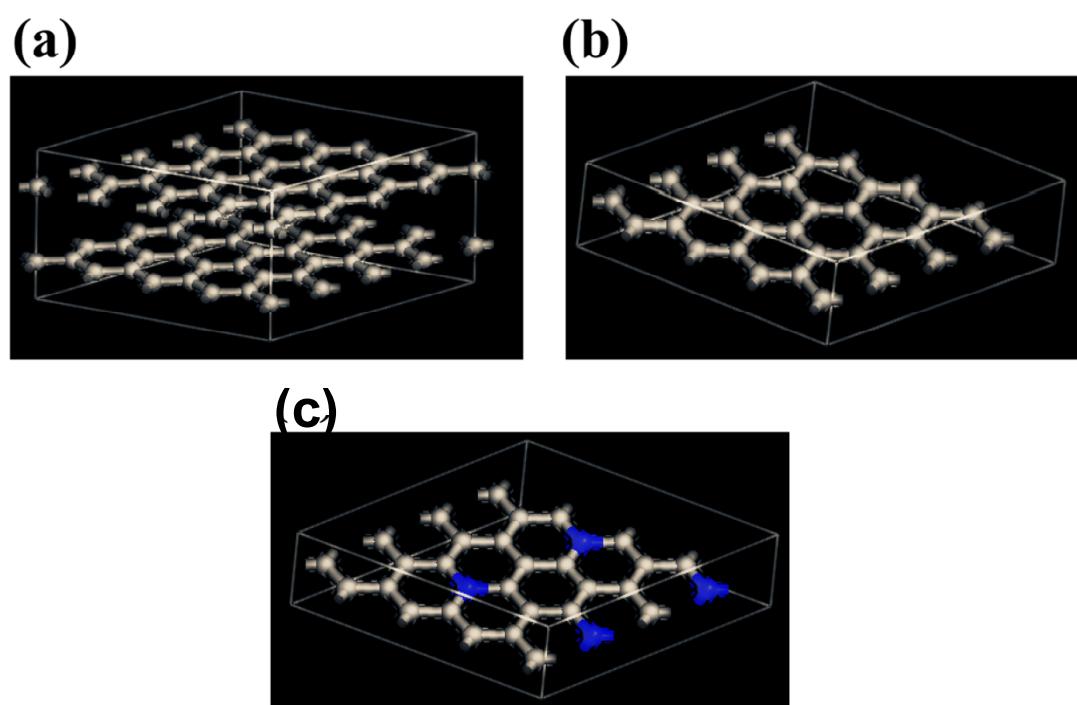


Fig. S7 The 3D structure of (a) graphite, (b) graphene, and (c) graphitic-N doped graphene. The gray color denotes bond, blue color denotes nitrogen atoms, and metal color denotes atoms.

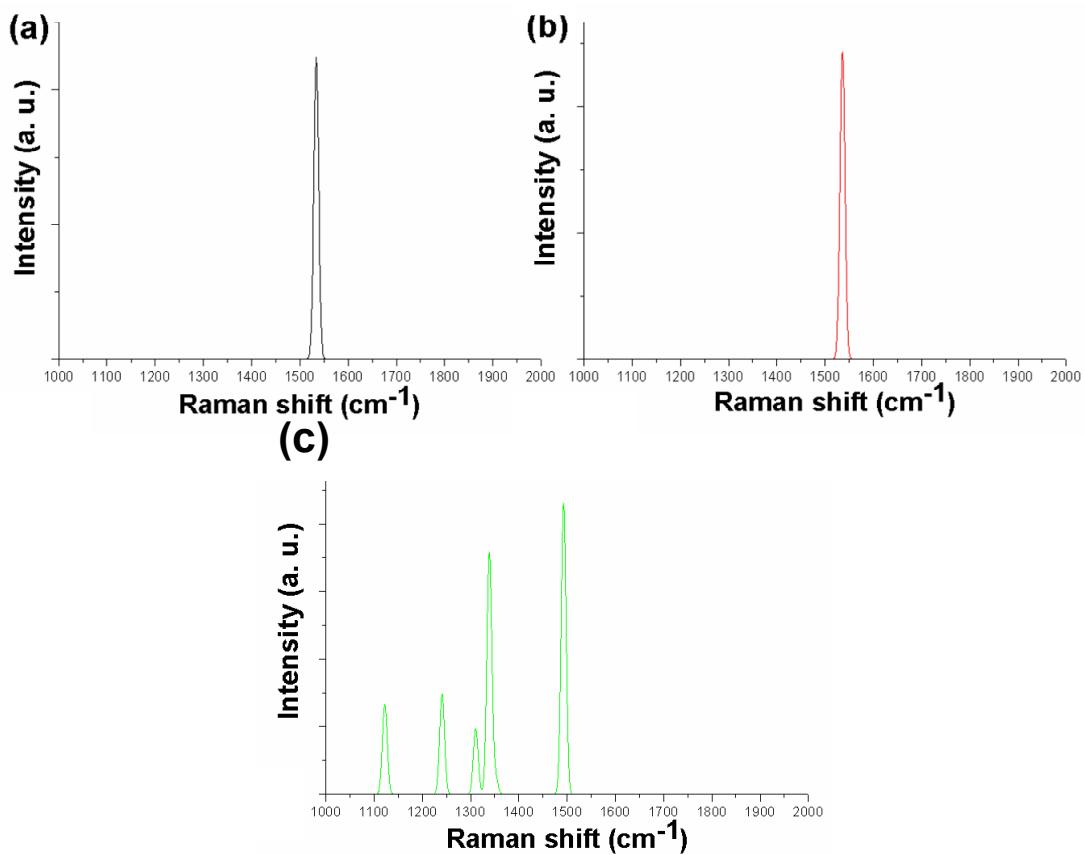


Fig. S8 Raman shift simulations of (a) graphite, (b) graphene and (c) graphitic N doped graphene based on their 3D structures in Fig. S7.

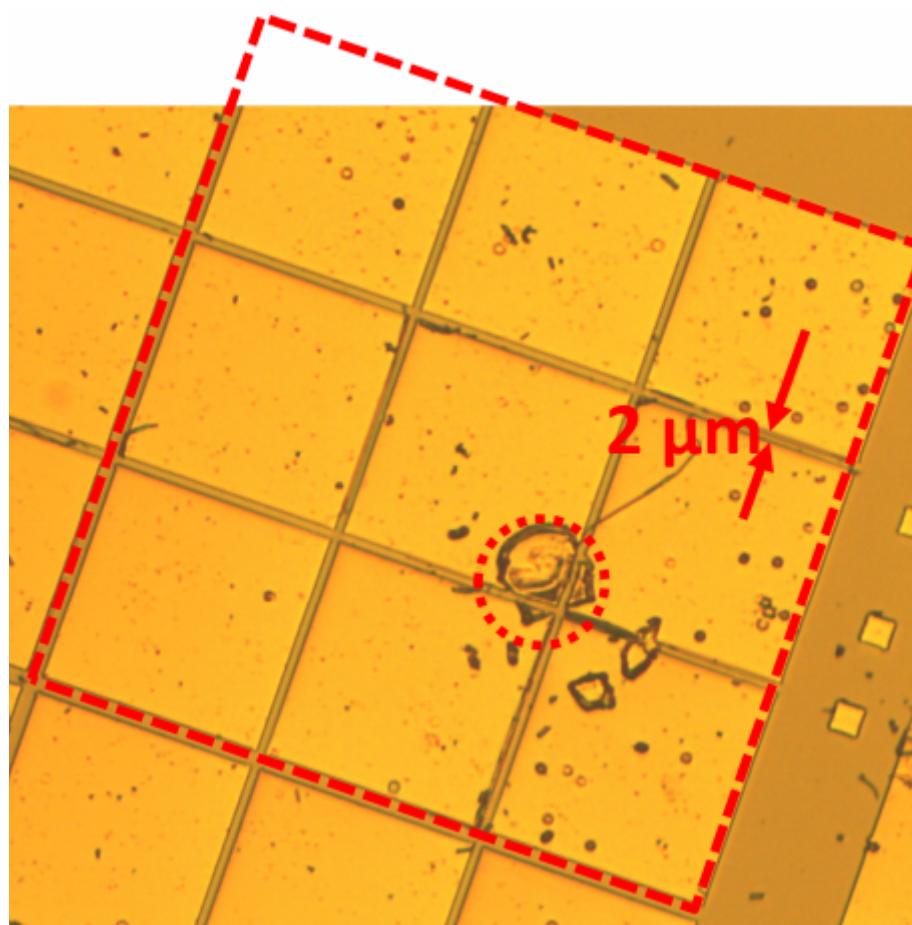


Fig. S9 (a) AFM image of the NG sheet device used for conductivity measurement.

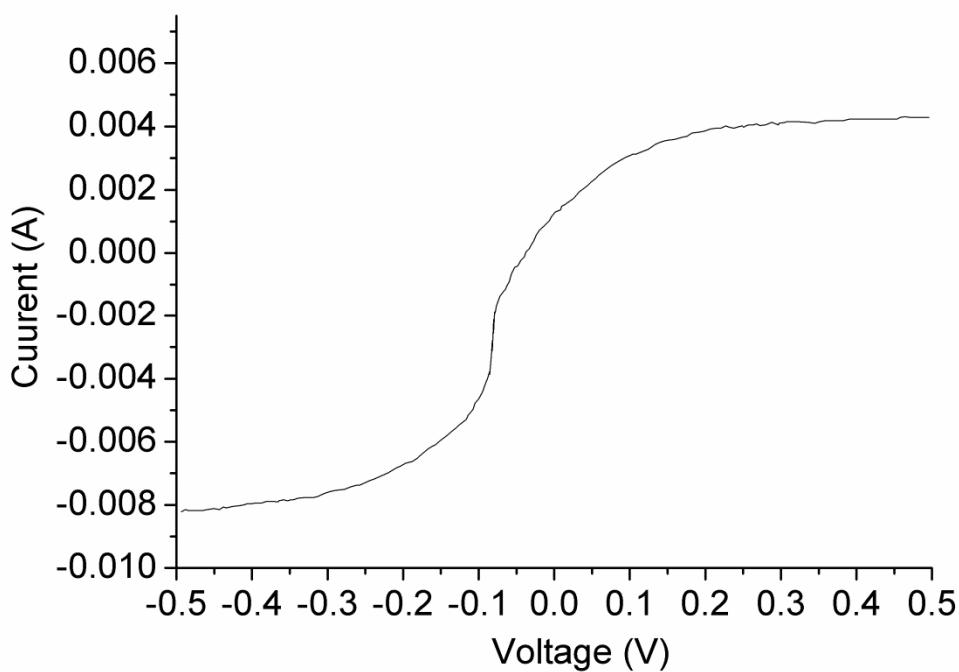


Fig. S10 The I-V curve of NG synthesized using [Bmim]Br.

According to Ohm's law for circuit theory, the resistance of a material is the applied voltage divided by the current drawn across the material across two electrodes.

$$R = V/I$$

Where:

R=Resistance (ohms, Ω)

V= Voltage (volts, V)

I = Current (amperes, A)

This electrical resistance is proportional to the sample's length and the resistivity and inversely proportional to the sample's cross sectional area.

$$R = \rho \frac{L}{A}$$

Where:

ρ = Resistivity

A =cross-sectional area (channel length \times thickness of graphene sheet)

L = length (graphene sheet width)

$$1.167 \times 10^2 \Omega = \rho \times (30 \mu\text{m}) / (30 \mu\text{m} \times 119.9 \text{ nm})$$

$$\rho = 1.4 \times 10^{-5} \Omega \cdot \text{m}$$

Table S2. Conductivity comparison between NG obtained in present work to reported NG and graphene

Method	Conductivity (S/m)	Reference
Thermal treatment	71500	Present work
Chemical reduction & thermal treatment	500	1
Chemical reduction	20000	2
Flash	2300	3
Chemical reduction	1000	4
Chemical reduction	0.023	5
Thermal treatment	200	6
Chemical reduction	2300	7
Chemical method, Vitamin C	687	8
Chemical method, Vitamin C	14.1	9
Chemical reduction	800	10
Supercritical alcohols	10638.3	11
hybrid Ag–MWNT composite	57	12
Chemical vapour deposition	500	13
CVD	0.00001	14
Liquid Exfoliation	20000	15

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